

Naoki Ohashi

List of Publications by Year in descending order

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370
papers

9,296
citations

71004

43
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62345

84
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379
all docs

379
docs citations

379
times ranked

10751
citing authors

#	ARTICLE	IF	CITATIONS
19	Experimental and theoretical investigation of crystal structure of formamidinium ⁺ copper ⁺ iodide single crystals grown from aqueous solution. <i>Journal of Solid State Chemistry</i> , 2021, 306, 122778.	1.4	2
20	Exploration of BaO ⁺ B ₂ O ₃ ⁺ Bi ₂ O ₃ glasses as sintering aids for BaTiO ₃ ceramics. <i>Ceramics International</i> , 2020, 46, 10233-10241.	2.3	6
21	Polar nano-region structure in the oxynitride perovskite LaTiO ₂ N. <i>Chemical Communications</i> , 2020, 56, 1385-1388.	2.2	7
22	Preparation and characterization of hollow silica nanocomposite functionalized with UV absorbable molybdenum cluster. <i>Advanced Powder Technology</i> , 2020, 31, 895-903.	2.0	8
23	Growth of germanium monosulfide (GeS) single crystal by vapor transport from molten GeS source using a two-zone horizontal furnace. <i>Journal of Crystal Growth</i> , 2020, 547, 125813.	0.7	4
24	Micrometer-scale monolayer SnS growth by physical vapor deposition. <i>Nanoscale</i> , 2020, 12, 23274-23281.	2.8	21
25	Zn-Al layered double hydroxide-based nanocomposite functionalized with an octahedral molybdenum cluster exhibiting prominent photoactive and oxidation properties. <i>Applied Clay Science</i> , 2020, 196, 105765.	2.6	16
26	High-Quality GaN Crystal Growth Using Flux-Film-Coated LPE with Na Flux. <i>Crystal Research and Technology</i> , 2020, 55, 2000042.	0.6	8
27	Zn-Al Layered Double Hydroxide Film Functionalized by a Luminescent Octahedral Molybdenum Cluster: Ultraviolet-Visible Photoconductivity Response. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 40495-40509.	4.0	15
28	Growth of Large Single Crystals of n-Type SnS from Halogen-Added Sn Flux. <i>Crystal Growth and Design</i> , 2020, 20, 5931-5939.	1.4	16
29	Inverse Perovskite Oxysilicides and Oxygermanides as Candidates for Nontoxic Infrared Semiconductor and Their Chemical Bonding Nature. <i>Inorganic Chemistry</i> , 2020, 59, 18305-18313.	1.9	4
30	Original Synthesis of Molybdenum Nitrides Using Metal Cluster Compounds as Precursors: Applications in Heterogeneous Catalysis. <i>Chemistry of Materials</i> , 2020, 32, 6026-6034.	3.2	11
31	Optical and structural investigations on titanium oxynitride films for visible-UV photocatalytic applications. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	3
32	Development of a flux-film-coated sputtering (FFC-sputtering) method for fabricating c-axis oriented AlN film. <i>AIP Advances</i> , 2020, 10, .	0.6	1
33	Structural and Thermal Properties in Formamidinium and Cs-Mixed Lead Halides. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 6967-6972.	2.1	31
34	Meso/macrospectically multifunctional surface interfaces, ridges, and vortex-modified anode/cathode cuticles as force-driven modulation of high-energy density of LIB electric vehicles. <i>Scientific Reports</i> , 2019, 9, 14701.	1.6	14
35	Achieving non-degenerate Zn ₃ N ₂ thin films by near room temperature sputtering deposition. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	7
36	Optoelectronic characteristics of the Ag-doped Si p-n photodiodes prepared by a facile thermal diffusion process. <i>AIP Advances</i> , 2019, 9, 055024.	0.6	4

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37	Silicon-compatible Mg ₂ Si/Si n-p photodiodes with high room temperature infrared responsivity. <i>Materials Science in Semiconductor Processing</i> , 2019, 102, 104577.	1.9	12
38	Effect of aging on the current transport properties at gold/niobium-doped strontium titanate Schottky junctions. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	4
39	Preparation of Proton Conductive Crystallized Tin Phosphate Glasses by Hydrothermal Treatments. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800355.	0.8	2
40	IR photoresponse characteristics of Mg ₂ Ge pn-junction photodiodes fabricated by rapid thermal annealing. <i>Journal of Alloys and Compounds</i> , 2019, 787, 578-584.	2.8	9
41	Suppressing the carrier concentration of zinc tin nitride thin films by excess zinc content and low temperature growth. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	14
42	Comprehensive first-principles study of AgGaO ₂ and CuGaO ₂ polymorphs. <i>Journal of the Ceramic Society of Japan</i> , 2019, 127, 339-347.	0.5	4
43	Ecofriendly Mg ₂ Si-based photodiode for short-wavelength IR sensing. <i>Materials Science in Semiconductor Processing</i> , 2019, 91, 222-229.	1.9	18
44	Growthâ€Parameter Dependence of Polarity and Electronic Transports in ZnO Thin Films Deposited by Magnetron Sputtering. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700838.	0.8	2
45	Sintering behavior and dielectric properties of BaTiO ₃ added with BaO-Bi ₂ O ₃ -B ₂ O ₃ glass phase. <i>Ceramics International</i> , 2018, 44, 13004-13010.	2.3	12
46	Observation of stacking faults and photoluminescence of laurate ion intercalated Zn/Al layered double hydroxide. <i>Materials Letters</i> , 2018, 213, 323-325.	1.3	8
47	Structure and Electron Mobility of ScN Films Grown on $\hat{\pm}$ -Al ₂ O ₃ (1    ) Tj ETQq _{1,1} 0.784314 rgBT (C) 1.3	1.3	7
48	Self-passivated ultra-thin SnS layers <i>via</i> mechanical exfoliation and post-oxidation. <i>Nanoscale</i> , 2018, 10, 22474-22483.	2.8	42
49	Preparation and some properties of Mg ₂ Si _{0.53} Ge _{0.47} single crystal and Mg ₂ Si _{0.53} Ge _{0.47} pn-junction diode. <i>AIP Advances</i> , 2018, 8, .	0.6	8
50	Extended Study on Electrophoretic Deposition Process of Inorganic Octahedral Metal Clusters: Advanced Multifunctional Transparent Nanocomposite Thin Films. <i>Bulletin of the Chemical Society of Japan</i> , 2018, 91, 1763-1774.	2.0	26
51	Controlling the electrical conductivity of ternary wurtzite-type and metastable $\hat{2}$ -AgGaO ₂ by impurity doping. <i>AIP Advances</i> , 2018, 8, 085203.	0.6	1
52	Electronic Transport Properties Governed by Polarity Control through Tailoring of ZnO Bilayer Structures. <i>Crystal Growth and Design</i> , 2018, 18, 5824-5831.	1.4	6
53	Piezoelectric Ca ₃ TaAl ₃ Si ₂ O ₁₄ (CTAS): High quality 2-in. single-crystal growth and electro-elastic properties from room to high (650â€°C) temperature. <i>Journal of Crystal Growth</i> , 2018, 501, 38-42.	0.7	6
54	Embedding hexanuclear tantalum bromide cluster {Ta ₆ Br ₁₂ } into SiO ₂ nanoparticles by reverse microemulsion method. <i>Heliyon</i> , 2018, 4, e00654.	1.4	9

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55	Electronic correlation in the quasi-two-dimensional electrider YCa_2C . Physical Review B, 2018, 98, .	1.1	21
56	Conditions for growth of AlN single crystals in Al-Sn flux. Journal of the American Ceramic Society, 2018, 101, 4876-4879.	1.9	3
57	Study design for control of HEART rate in infant and child tachyarrhythmia with heart failure Using Landiolol (HEARTFUL): A prospective, multicenter, uncontrolled clinical trial. Journal of Cardiology, 2017, 70, 232-237.	0.8	7
58	Potential barrier formed at domain boundaries in twinned tetragonal BaTiO ₃ single crystals. Applied Physics Letters, 2017, 110, .	1.5	8
59	Crystalline polarity of ZnO thin films deposited under dc external bias on various substrates. Journal of Crystal Growth, 2017, 463, 38-45.	0.7	6
60	Formation Mechanism of Transparent Mo ₆ Metal Atom Cluster Film Prepared by Electrophoretic Deposition. Journal of the Electrochemical Society, 2017, 164, D412-D418.	1.3	18
61	Lattice and Valence Electronic Structures of Crystalline Octahedral Molybdenum Halide Clusters-Based Compounds, Cs ₂ [Mo ₆ X ₁₄] (X = Cl, Br, I), Studied by Density Functional Theory Calculations. Inorganic Chemistry, 2017, 56, 6234-6243.	1.9	16
62	Multiple Roles of Hydrogen Treatments in Amorphous InGaZnO Films. ECS Journal of Solid State Science and Technology, 2017, 6, P365-P372.	0.9	30
63	Bushy sphere dendrites with husk-shaped branches axially spreading out from the core for photo-catalytic oxidation/remediation of toxins. Nanoscale, 2017, 9, 7947-7959.	2.8	36
64	Effective, Low-Cost Recovery of Toxic Arsenate Anions from Water by Using Hollow-Sphere Geode Traps. Chemistry - an Asian Journal, 2017, 12, 1952-1964.	1.7	36
65	Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. NPC Asia Materials, 2017, 9, e359-e359.	3.8	89
66	From Cs ₂ Mo ₆ Cl ₁₄ to Cs ₂ Mo ₆ Cl ₁₄ ·H ₂ O and Vice Versa: Crystal Chemistry Investigations. Journal of Cluster Science, 2017, 28, 773-798.	1.7	13
67	New ultra-violet and near-infrared blocking filters for energy saving applications: fabrication of tantalum metal atom cluster-based nanocomposite thin films by electrophoretic deposition. Journal of Materials Chemistry C, 2017, 5, 10477-10484.	2.7	41
68	Solvent-mediated purification of hexa-molybdenum cluster halide, Cs ₂ [Mo ₆ Cl ₁₄] for enhanced optical properties. CrystEngComm, 2017, 19, 6028-6038.	1.3	8
69	Variation of crystal structure and optical properties of wurtzite-type oxide semiconductor alloys of $\text{In}_2\text{Cu}(\text{Ga},\text{Al})\text{O}_2$. Journal of Applied Physics, 2017, 121, .	1.1	8
70	Transparent tantalum cluster-based UV and IR blocking electrochromic devices. Journal of Materials Chemistry C, 2017, 5, 8160-8168.	2.7	25
71	P μ 3: Quantitative Analysis and Deconvolution of Subgap States in Amorphous InGaZnO. Digest of Technical Papers SID International Symposium, 2017, 48, 1273-1275.	0.1	1
72	Heteroepitaxial growth and electric properties of (110)-oriented scandium nitride films. Journal of Crystal Growth, 2017, 476, 12-16.	0.7	7

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73	Mo ₆ cluster-based compounds for energy conversion applications: comparative study of photoluminescence and cathodoluminescence. <i>Science and Technology of Advanced Materials</i> , 2017, 18, 458-466.	2.8	37
74	Wurtzite-Derived Quaternary Oxide Semiconductor Cu ₂ ZnGeO ₄ : Its Structural Characteristics, Optical Properties, and Electronic Structure. <i>Inorganic Chemistry</i> , 2017, 56, 14277-14283.	1.9	6
75	Semimetallic bands derived from interlayer electrons in the quasi-two-dimensional electride Y_2C . <i>Physical Review B</i> , 2017, 96, .	1.1	17
76	Resistivity and piezoelectric properties of Ca ₃ TaGa _{1.5} Al _{1.5} Si ₂ O ₁₄ single crystals for high temperature sensors. <i>RSC Advances</i> , 2017, 7, 56697-56703.	1.7	3
77	Simulation of crystal and electronic structures of octahedral molybdenum cluster complex compound Cs ₂ [Mo ₆ Cl ₁₄] using various DFT functionals. <i>Journal of the Ceramic Society of Japan</i> , 2017, 125, 753-759.	0.5	5
78	Electrophoretic Coating of Octahedral Molybdenum Metal Clusters for UV/NIR Light Screening. <i>Coatings</i> , 2017, 7, 114.	1.2	13
79	Temperature dependence of electrical resistivity, dielectric and piezoelectric properties of Ca ₃ TaGa _{3-x} Al _x Si ₂ O ₁₄ single crystals as a function of Al content. <i>Journal of Alloys and Compounds</i> , 2016, 687, 797-803.	2.8	12
80	Quantitative secondary ion mass spectrometric analysis of secondary ion polarity in GaN films implanted with oxygen. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 101001.	0.8	3
81	Isotope tracer investigation and ab-initio simulation of anisotropic hydrogen transport and possible multi-hydrogen centers in tin dioxide. <i>Journal of Applied Physics</i> , 2016, 119, 225704.	1.1	4
82	First principles calculations of ternary wurtzite \hat{I}^2 -CuGaO ₂ . <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	21
83	Floating zone growth and magnetic properties of Y ₂ C two-dimensional electride. <i>Journal of Crystal Growth</i> , 2016, 454, 15-18.	0.7	16
84	Fabrication of Transparent Thin Film of Octahedral Molybdenum Metal Clusters by Electrophoretic Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, R178-R186.	0.9	18
85	Inorganic Molybdenum Clusters as Light Harvesters in All Inorganic Solar Cells: A Proof of Concept. <i>ChemistrySelect</i> , 2016, 1, 2284-2289.	0.7	35
86	Visible tunable lighting system based on polymer composites embedding ZnO and metallic clusters: from colloids to thin films. <i>Science and Technology of Advanced Materials</i> , 2016, 17, 443-453.	2.8	25
87	Influence of growth conditions on the optical, electrical resistivity and piezoelectric properties of Ca ₃ TaGa ₃ Si ₂ O ₁₄ single crystals. <i>Journal of the Ceramic Society of Japan</i> , 2016, 124, 523-527.	0.5	23
88	First-Principles Study of CuGaO ₂ Polymorphs: Delafossite \hat{I}^2 -CuGaO ₂ and Wurtzite \hat{I}^2 -CuGaO ₂ . <i>Inorganic Chemistry</i> , 2016, 55, 7610-7616.	1.9	29
89	Theoretical and experimental determination of the crystal structures of cesium molybdenum chloride. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 075502.	0.8	12
90	Pulverization of oxide powders utilizing thermal treatment in ammonia-based atmosphere. <i>Journal of the European Ceramic Society</i> , 2016, 36, 4083-4088.	2.8	4

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91	Effects of thermal annealing on elimination of deep defects in amorphous In ⁺ Ga ⁺ Zn ⁺ O thin-film transistors. Thin Solid Films, 2016, 614, 73-78.	0.8	13
92	Influence of Oxygen Partial Pressure during Growth on Optical and Electrical Properties of Ca ₃ TaAl ₃ Si ₂ O ₁₄ Single Crystals. Crystal Growth and Design, 2016, 16, 2151-2156.	1.4	16
93	Investigating crystalline-polarity-dependent electronic structures of GaN by hard x-ray photoemission and <i>ab-initio</i> calculations. Applied Physics Letters, 2015, 107, .	1.5	17
94	Effects of residual hydrogen in sputtering atmosphere on structures and properties of amorphous In-Ga-Zn-O thin films. Journal of Applied Physics, 2015, 118, .	1.1	34
95	Electric field and temperature dependence of dielectric permittivity in strontium titanate investigated by a photoemission study on Pt/SrTiO ₃ :Nb junctions. Applied Physics Letters, 2015, 106, .	1.5	12
96	Thermal and piezoelectric properties of La ₃ Ta _{0.5} Ga _{5.1} Al _{0.4} O ₁₄ (LTGA) for high temperature sensors. Journal of Alloys and Compounds, 2015, 647, 1086-1090.	2.8	17
97	Inorganic Molybdenum Octahedral Nanosized Cluster Units, Versatile Functional Building Block for Nanoarchitectonics. Journal of Inorganic and Organometallic Polymers and Materials, 2015, 25, 189-204.	1.9	102
98	Transparent ZnO Films Deposited by Aqueous Solution Process Under Various pH Conditions. Journal of Electronic Materials, 2015, 44, 2657-2662.	1.0	7
99	Charge Compensation by Excess Oxygen in Amorphous In ⁺ Ga ⁺ Zn ⁺ O Films Deposited by Pulsed Laser Deposition. Journal of Display Technology, 2015, 11, 518-522.	1.3	26
100	AgBiS ₂ single crystal grown using slow cooling method and its characterization. Journal of Crystal Growth, 2015, 411, 1-3.	0.7	15
101	Impact of Electrode Oxidation on the Current Transport Properties at Platinum/(Niobium-Doped) Tj ETQq1 1 0.784314 rgBT /Overlock P243-P248.	0.9	9
102	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. ECS Journal of Solid State Science and Technology, 2014, 3, Q3085-Q3090.	0.9	50
103	Investigation of charge compensation in indium-doped tin dioxide by hydrogen insertion via annealing under humid conditions. Applied Physics Letters, 2014, 104, .	1.5	3
104	SnS crystal grown using horizontal gradient freeze method and its electrical properties. Journal of Alloys and Compounds, 2014, 591, 326-328.	2.8	11
105	Wurtzite CuGaO ₂ : A New Direct and Narrow Band Gap Oxide Semiconductor Applicable as a Solar Cell Absorber. Journal of the American Chemical Society, 2014, 136, 3378-3381.	6.6	85
106	Effect of crystalline polarity on microstructure and optoelectronic properties of gallium-doped zinc oxide films deposited onto glass substrates. Thin Solid Films, 2014, 552, 56-61.	0.8	17
107	Surface segregation of W doped in ZnO thin films. Surface Science, 2014, 625, 1-6.	0.8	8
108	Multi-Functional Silica Nanoparticles Based on Metal Atom Clusters: From Design to Toxicological Studies. Key Engineering Materials, 2014, 617, 179-183.	0.4	1

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109	Hydrogen in tin dioxide films and bulk ceramics: An attempt to identify the most hidden impurity. Applied Physics Letters, 2014, 104, 042110.	1.5	12
110	Floating zone growth of cerium tetra-boride crystals. Journal of the Ceramic Society of Japan, 2014, 122, 192-194.	0.5	0
111	Effects of dielectric film surface on oxygen diffusion. Journal of the Ceramic Society of Japan, 2014, 122, 410-414.	0.5	1
112	Electrical and optical properties of W-doped ZnO films grown on (111) sapphire substrates using pulsed laser deposition. Journal of the Ceramic Society of Japan, 2014, 122, 908-913.	0.5	9
113	Zn and Sb interaction and oxygen defect chemistry in dense SnO ₂ ceramics co-doped with ZnO and Sb ₂ O ₅ . Journal of the Ceramic Society of Japan, 2014, 122, 421-425.	0.5	4
114	Bulk, interface and surface properties of zinc oxide. Journal of the Ceramic Society of Japan, 2014, 122, 530-536.	0.5	7
115	Enhanced ethanol-gas sensing performance of Ce-doped SnO ₂ hollow nanofibers prepared by electrospinning. Sensors and Actuators B: Chemical, 2013, 188, 872-878.	4.0	86
116	Electrical properties of scandium nitride epitaxial films grown on (100) magnesium oxide substrates by molecular beam epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	30
117	Tunable Visible Emission of Luminescent Hybrid Nanoparticles Incorporating Two Complementary Luminophores: ZnO Nanocrystals and [Mo ₆ Br ₁₄] ²⁺ Nanosized Cluster Units. Particle and Particle Systems Characterization, 2013, 30, 90-95.	1.2	25
118	Luminescence: Tunable Visible Emission of Luminescent Hybrid Nanoparticles Incorporating Two Complementary Luminophores: ZnO Nanocrystals and [Mo ₆ Br ₁₄] ²⁺ Nanosized Cluster Units (Part. Part. Syst. Charact.) Tj ETQq000 rgBT/Overlock 12	1.2	25
119	The effect of n- and p-type doping on coherent phonons in GaN. Journal of Physics Condensed Matter, 2013, 25, 205404.	0.7	11
120	Extended Investigations on Luminescent Cs ₂ [Mo ₆ Br ₁₄] ₂ @SiO ₂ Nanoparticles: Physico-Structural Characterizations and Toxicity Studies. Journal of Physical Chemistry C, 2013, 117, 20154-20163.	1.5	68
121	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. Applied Physics Letters, 2013, 103, 201904.	1.5	28
122	Polarity control of intrinsic ZnO films using substrate bias. Applied Physics Letters, 2013, 103, .	1.5	15
123	Ion implantation and diffusion of zinc in dense SnO ₂ ceramics. Journal of the Ceramic Society of Japan, 2013, 121, 1004-1007.	0.5	5
124	Preparation of Ni ₂ P and Fe ₂ P single crystals by the floating-zone method. Journal of the Ceramic Society of Japan, 2013, 121, 331-332.	0.5	9
125	Characterization of oxygen defect and zinc segregation in the dense tin dioxide ceramics added with zinc oxide. Journal of the Ceramic Society of Japan, 2013, 121, 956-959.	0.5	6
126	Influence of crystal polarity on Mg incorporation in ZnO. Physica Status Solidi (B): Basic Research, 2013, 250, 2122-2125.	0.7	11

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127	Crystal Polarity and Electrical Properties of Heavily Doped ZnO Films. Materials Research Society Symposia Proceedings, 2012, 1494, 133-138.	0.1	3
128	Polarity-dependent photoemission spectra of wurtzite-type zinc oxide. Applied Physics Letters, 2012, 100, .	1.5	32
129	Evidence of Eu ²⁺ 4 <i>f</i> electrons in the valence band spectra of EuTiO ₃ and EuZrO ₃ . Journal of Applied Physics, 2012, 112, .	1.1	28
130	Observation and simulation of hard x ray photoelectron diffraction to determine polarity of polycrystalline zinc oxide films with rotation domains. Journal of Applied Physics, 2012, 111, 033525.	1.1	13
131	Influence of substrate nitridation on GaN and InN growth by plasma-assisted molecular-beam epitaxy. Journal of the Ceramic Society of Japan, 2012, 120, 513-519.	0.5	3
132	Oxygen Diffusion Phenomena and Hydrogen Incorporation in Reducing BaTiO ₃ Ceramics Doped with Ho below Solubility Limit. Japanese Journal of Applied Physics, 2012, 51, 101801.	0.8	4
133	An aqueous solution process and subsequent UV treatment for highly transparent conductive ZnO films. Journal of Materials Chemistry, 2012, 22, 20706.	6.7	35
134	Evaluation of zinc self-diffusion at the interface between homoepitaxial ZnO thin films and (0001) ZnO substrates. Solid State Communications, 2012, 152, 1917-1920.	0.9	3
135	Determination of Schottky barrier profile at Pt/SrTiO ₃ :Nb junction by x-ray photoemission. Applied Physics Letters, 2012, 101, .	1.5	27
136	Fabricating transparent waveguide for wireless communication. Thin Solid Films, 2012, 520, 3835-3838.	0.8	0
137	Oxygen Diffusion Phenomena and Hydrogen Incorporation in Reducing BaTiO ₃ Ceramics Doped with Ho below Solubility Limit. Japanese Journal of Applied Physics, 2012, 51, 101801.	0.8	2
138	Visualization of Grain Boundary as Blocking Layer for Oxygen Tracer Diffusion and a Proposed Defect Model in Non Doped BaTiO ₃ Ceramics. Applied Physics Express, 2011, 4, 055801.	1.1	15
139	XPS study of Sb-/In-doping and surface pinning effects on the Fermi level in SnO ₂ (101) thin films. Applied Physics Letters, 2011, 98, .	1.5	38
140	Photocatalytic Activity and Related Surface Properties of Transparent ZnO Films Prepared by a Low-temperature Aqueous Route. Photochemistry and Photobiology, 2011, 87, 1009-1015.	1.3	7
141	Heat capacity and thermodynamic properties of germanium disulfide at temperatures from T=(2 to) T _J ETQq1 1 0.784314 rgBT /Overl	1.0	7
142	Cation diffusion along basal dislocations in sapphire. Acta Materialia, 2011, 59, 1105-1111.	3.8	6
143	Excitation photon energy dependence of the relaxation processes of the photoexcited states in a quasi-one-dimensional halogen bridged Pt complex. Physics Procedia, 2011, 13, 66-69.	1.2	0
144	Polarity determination of wurtzite-type crystals using hard x-ray photoelectron diffraction. Surface Science, 2011, 605, 1336-1340.	0.8	19

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145	Polarity of heavily doped ZnO films grown on sapphire and SiO ₂ glass substrates by pulsed laser deposition. <i>Thin Solid Films</i> , 2011, 519, 5875-5881.	0.8	29
146	Electric property of ZnO based transparent conductor films in GHz range. <i>IOP Conference Series: Materials Science and Engineering</i> , 2011, 18, 092051.	0.3	1
147	Simultaneous Diffusion of Oxygen Tracer and Lithium Impurity in Aluminum Doped Zinc Oxide. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 125501.	0.8	3
148	Temperature dependence of carrier transport and resistance switching in Pt/SrTi _{1-x} Nb _x O ₃ Schottky junctions. <i>Physical Review B</i> , 2011, 83, .	1.1	35
149	Defects in ZnO transparent conductors studied by capacitance transients at ZnO/Si interface. <i>Applied Physics Letters</i> , 2011, 98, 082101.	1.5	18
150	Focus on Advanced Ceramics. <i>Science and Technology of Advanced Materials</i> , 2011, 12, 030301.	2.8	0
151	Simultaneous Diffusion of Oxygen Tracer and Lithium Impurity in Aluminum Doped Zinc Oxide. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 125501.	0.8	5
152	Effect of post-annealing on structural and optical properties, and elemental distribution in heavy Eu-implanted ZnO thin films. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 1087-1089.	0.5	3
153	Investigation on buffer layer for InN growth by molecular beam epitaxy. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 152-156.	0.5	1
154	Development of ZnO-based surface plasmon resonance gas sensor and analysis of UV irradiation effect on NO ₂ desorption from ZnO thin films. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 193-196.	0.5	18
155	Ion implantation and diffusion behavior of silver in zinc oxide. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 217-219.	0.5	12
156	Oxygen tracer diffusion in magnesium-doped ZnO ceramics. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 362-365.	0.5	10
157	Synthesis of highly dense and fine-grained aggregates of mantle composites by vacuum sintering of nano-sized mineral powders. <i>Physics and Chemistry of Minerals</i> , 2010, 37, 505-518.	0.3	51
158	Nitrogen isotopic effect in Ga ₁₅ N epilayers grown by plasma-assisted molecular-beam epitaxy. <i>Scripta Materialia</i> , 2010, 62, 516-519.	2.6	1
159	ZnO-based visible-light photocatalyst: Band-gap engineering and multi-electron reduction by co-catalyst. <i>Applied Catalysis B: Environmental</i> , 2010, 100, 502-509.	10.8	155
160	Fabrication and hard X-ray photoemission analysis of photocathodes with sharp solar-blind sensitivity using AlGaIn films grown on Si substrates. <i>Applied Surface Science</i> , 2010, 256, 4442-4446.	3.1	43
161	Preparation and characterization of Zn ¹⁸ O/Zn ¹⁶ O isotope heterostructure thin films. <i>Journal of the European Ceramic Society</i> , 2010, 30, 423-428.	2.8	3
162	Resistance switching properties in Pt/SrTiO ₃ :Nb Schottky junctions studied by admittance spectroscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 173, 216-219.	1.7	12

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